



LINEAR INTEGRATED CIRCUITS

7929225 S G S SEMICONDUCTOR CORP

TV VERTICAL DEFLECTION SYSTEM

The TDA 1170S is a monolithic integrated circuit in a 12-lead quad in-line plastic package. It is intended for use in black and white and colour TV receivers.

The functions incorporated are:

- synchronization circuit
- oscillator and ramp generator
- high power gain amplifier
- flyback generator
- voltage regulator

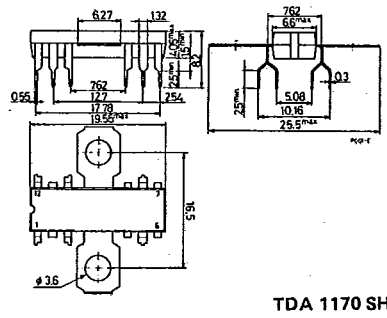
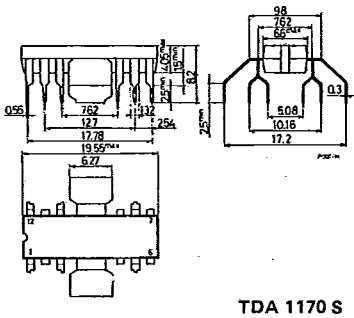
ABSOLUTE MAXIMUM RATINGS

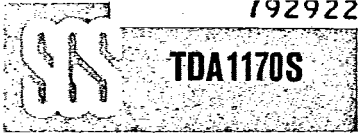
V_s	Supply voltage at pin 2	35	V
V_4, V_5	Flyback peak voltage	60	V
V_{10}	Power amplifier input voltage	+ 10	V
		- 0.5	V
I_o	Output peak current (non repetitive) at $t = 2$ msec	2	A
I_o	Output peak current at $f = 50$ Hz $t \leq 10$ μ sec	2.5	A
I_o	Output peak current at $f = 50$ Hz $t > 10$ μ sec	1.5	A
I_3	Pin 3 DC current at $V_4 < V_2$	100	mA
I_3	Pin 3 peak to peak flyback current for $f = 50$ Hz, $t_{fly} \leq 1.5$ msec	1.8	A
I_8	Pin 8 current	± 20	mA
P_{tot}	Power dissipation: at $T_{tab} = 90^\circ\text{C}$	5	W
	at $T_{amb} = 80^\circ\text{C}$	1	W
T_{stg}, T_j	Storage and junction temperature	-40 to 150	$^\circ\text{C}$

ORDERING NUMBERS: TDA 1170 S
TDA 1170 SH

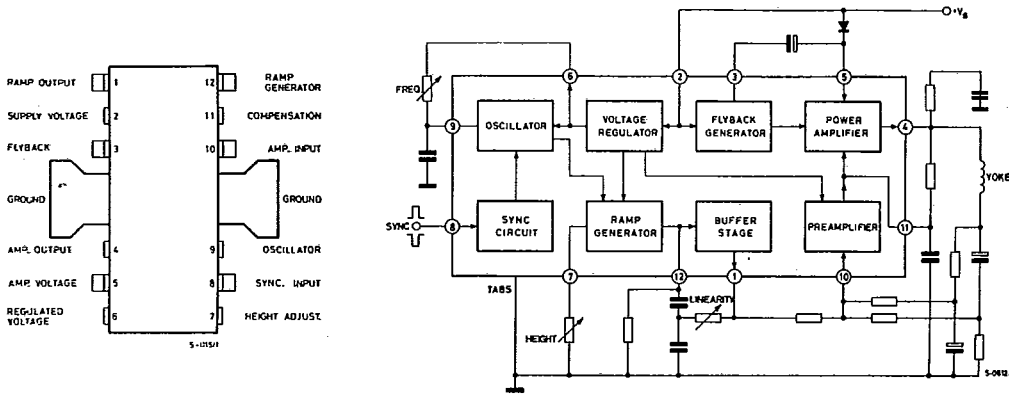
MECHANICAL DATA

Dimensions in mm

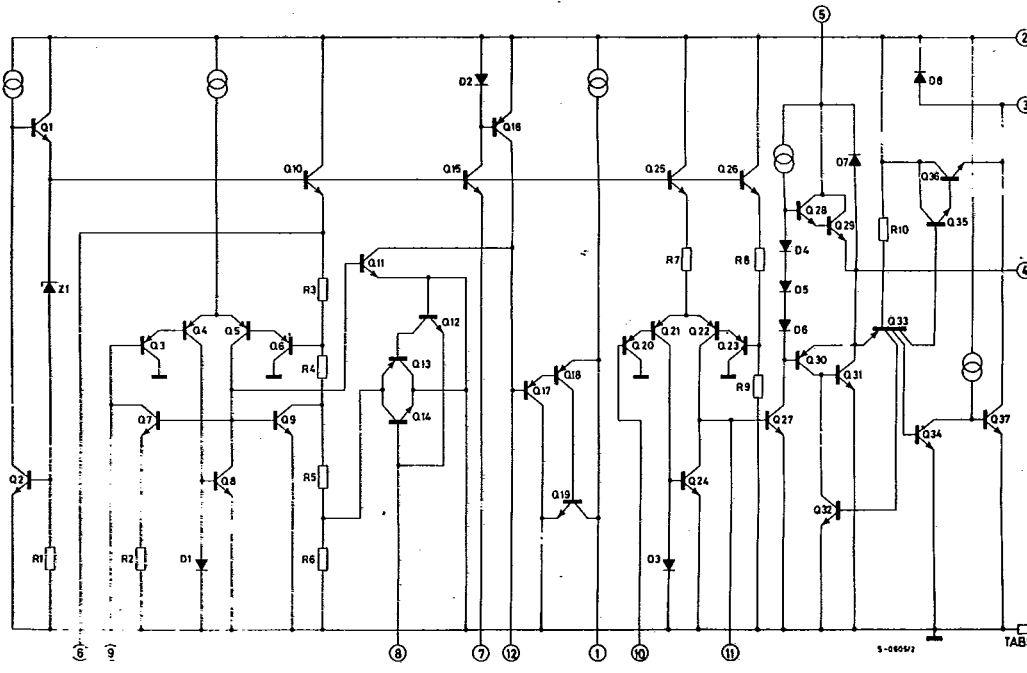




CONNECTION AND BLOCK DIAGRAMS



SCHEMATIC DIAGRAM





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THERMAL DATA

		TDA 1170S	TDA 1170SH
$R_{th\ j-tab}$	Thermal resistance junction-tab	max 12°C/W	max 10°C/W
$R_{th\ j-amb}$	Thermal resistance junction-ambient	max 70°C/W(°)	max 80°C/W

(a) Obtained with tabs soldered to printed circuit with minimized copper area.

ELECTRICAL CHARACTERISTICS (Refer to the test circuits, $V_s=35V$, $T_{amb}=25^\circ C$, unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit	Fig.
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DC CHARACTERISTICS

I_2	Pin 2 quiescent current	$I_3 = 0$		7	14	mA	1b
I_5	Pin 5 quiescent current	$I_4 = 0$		8	15	mA	1b
$-I_9$	Oscillator bias current	$V_9 = 1V$		0.1	1	μA	1a
$-I_{10}$	Amplifier input bias current	$V_{10} = 1V$		0.1	1	μA	1b
$-I_{12}$	Ramp generator bias current	$V_{12} = 0$		0.02	0.3	μA	1a
$-I_{12}$	Ramp generator current	$I_7 = 20\ \mu A$ $V_{12} = 0$	19	20	24	μA	1b
$\frac{\Delta I_{12}}{I_{12}}$	Ramp generator non-linearity	$\Delta V_{12} = 0$ to 12V $I_7 = 20\ \mu A$		0.2	1	%	1b
V_s	Supply voltage range		10		36	V	—
V_1	Pin 1 saturation voltage to ground	$I_1 = 1\ mA$		1	1.4	V	—
V_3	Pin 3 saturation voltage to ground	$I_3 = 10\ mA$		1.7	2.6	V	1a
V_4	Quiescent output voltage	$V_s = 10V$ $R_1 = 10\ K\Omega$ $R_2 = 10\ K\Omega$	4.17	4.4	4.63	V	1a
		$V_s = 35V$ $R_1 = 30\ K\Omega$ $R_2 = 10\ K\Omega$	8.35	8.8	9.25	V	1a
V_{4L}	Output saturation voltage to ground	$-I_4 = 0.1A$		0.9	1.2	V	1c
		$-I_4 = 0.8A$		1.9	2.3	V	1c
V_{4H}	Output saturation voltage to supply	$I_4 = 0.1A$		1.4	2.1	V	1d
		$I_4 = 0.8A$		2.8	3.2	V	1d
V_6	Regulated voltage at pin 6		6.1	6.5	6.9	V	1b
V_7	Regulated voltage at pin 7	$I_7 = 20\ \mu A$	6.2	6.6	7	V	1b
$\frac{\Delta V_6}{\Delta V_s}; \frac{\Delta V_7}{\Delta V_s}$	Regulated voltage drift with supply voltage	$\Delta V_s = 10$ to 35V		1		mV/V	1b
V_{10}	Amplifier input reference voltage		2.07	2.2	2.3	V	—
R_8	Pin 8 input resistance	$V_8 \leq 0.4V$	1			$M\Omega$	1a

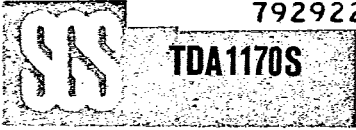


Fig. 1 - DC test circuits

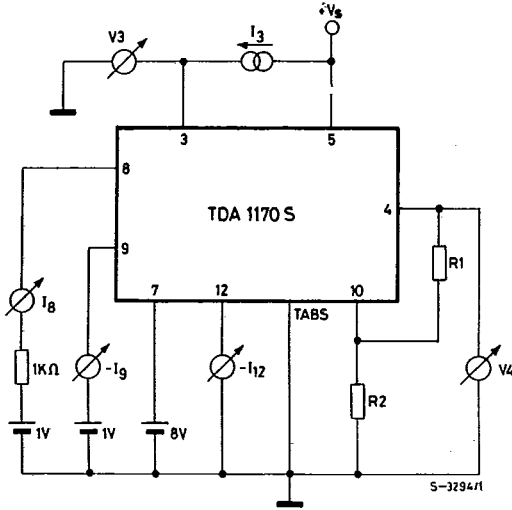


Fig. 1a

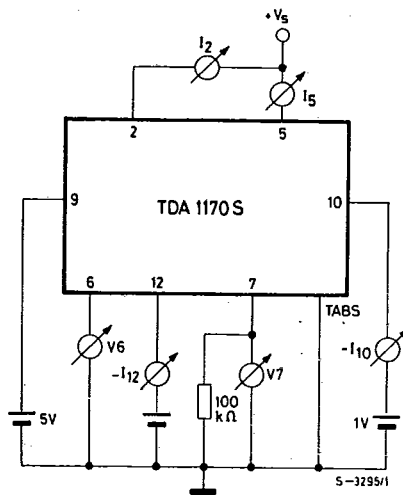


Fig. 1b

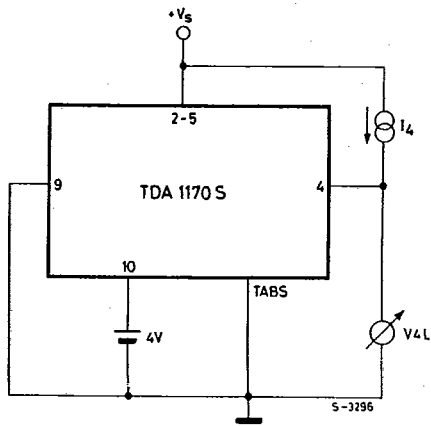


Fig. 1c

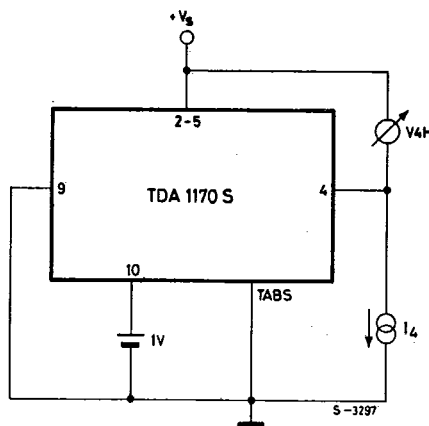


Fig. 1d

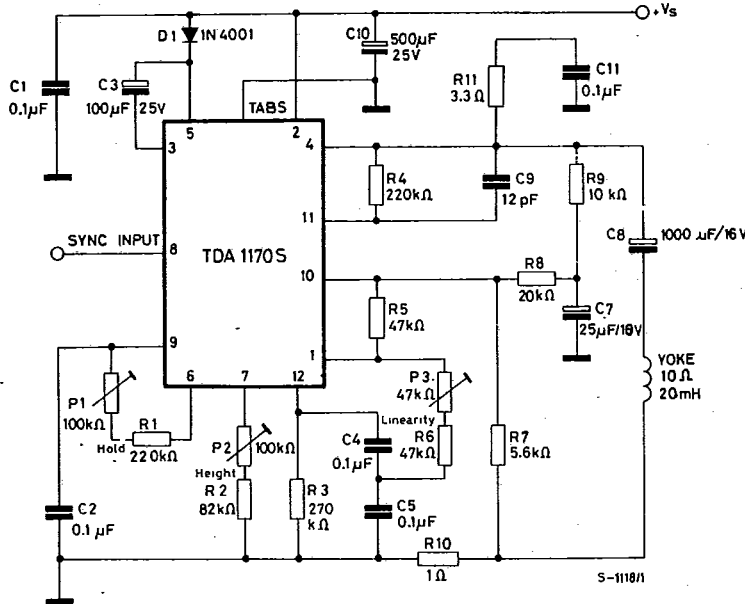


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AC CHARACTERISTICS (Refer to the test circuit, $V_s = 25V$; $f = 50\text{ Hz}$; $T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit	Fig.
I_s	Supply current		140		mA	2
I_b	Sync. input current (positive or negative)	500			μA	2
V_4	Flyback voltage		51		V	2
V_9	Peak to peak oscillator sawtooth voltage		2.4		V	2
t_{fly}	Flyback time		0.7		ms	2
f_o	Free running frequency	$(P_1 + R_1) = 300\text{ K}\Omega$ $C_2 = 100\text{ nF}$	44		Hz	2
		$(P_1 + R_1) = 260\text{ K}\Omega$ $C_2 = 100\text{ nF}$	52		Hz	2
Δf	Synchronization range	14			Hz	2
$\frac{\Delta f}{\Delta V_s}$	Frequency drift with supply voltage		0.005		Hz/V	2
$\frac{\Delta f}{\Delta T_{tab}}$	Frequency drift with tab temperature		0.01		Hz/ $^\circ\text{C}$	2

Fig. 2 - AC test circuit



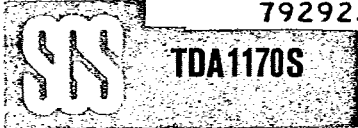
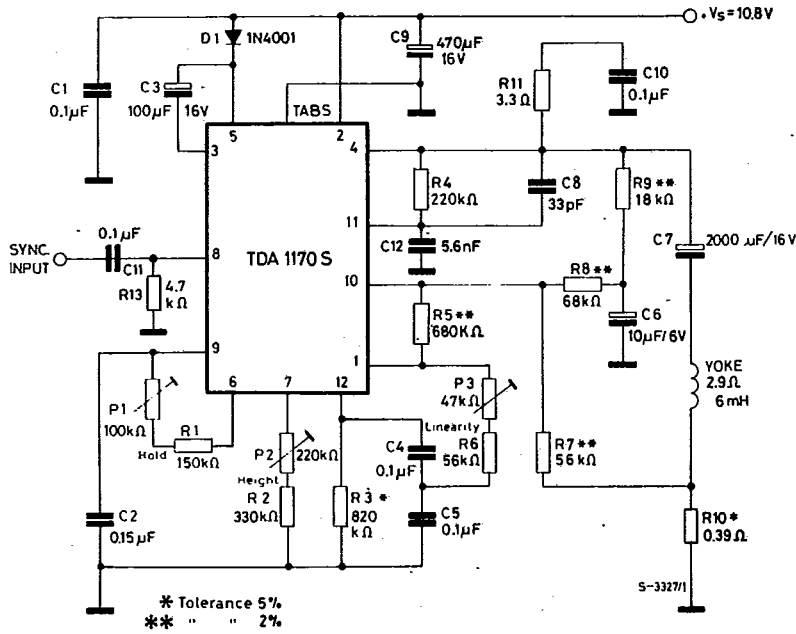


Fig. 3 - Typical application circuit for small screen B/W TV set ($R_y = 2.9\Omega$, $L_y = 6\text{ mH}$; $I_y = 1.1\text{ App}$)



Typical performance

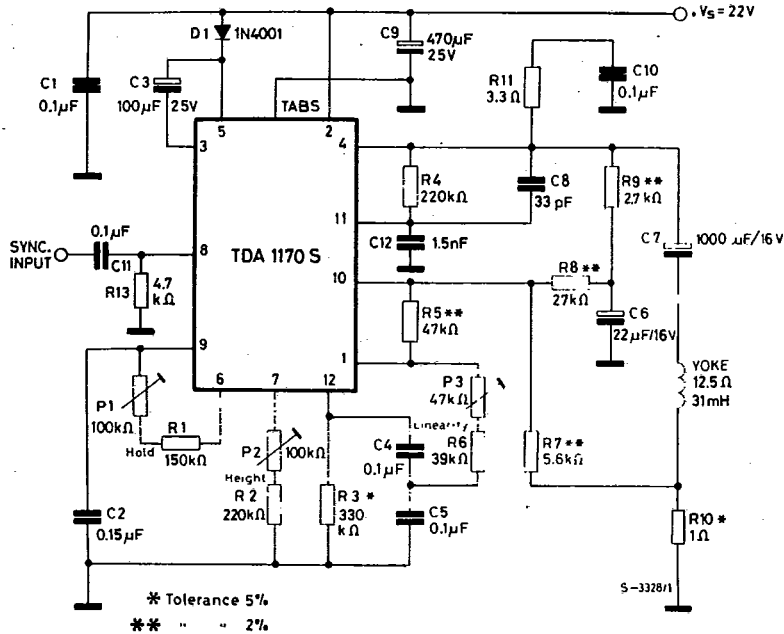
V_s	Operating supply voltage	10.8	V
I_s	Supply current	155	mA
t_{fly}	Flyback time	0.5	ms
P_{tot}	TDA 1170S power dissipation	1.35	W
I_y	Maximum scanning current (peak to peak)	1.30	A

For safe working up to $T_{amb} = 60^\circ\text{C}$ a heatsink of $R_{th} = 30^\circ\text{C/W}$ is required.



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Fig. 4 - Typical application circuit for small screen 90° PIL TVC set ($R_y = 12.5\Omega$; $L_y = 31\text{ mH}$; $I_y = 0.8\text{ App}$)



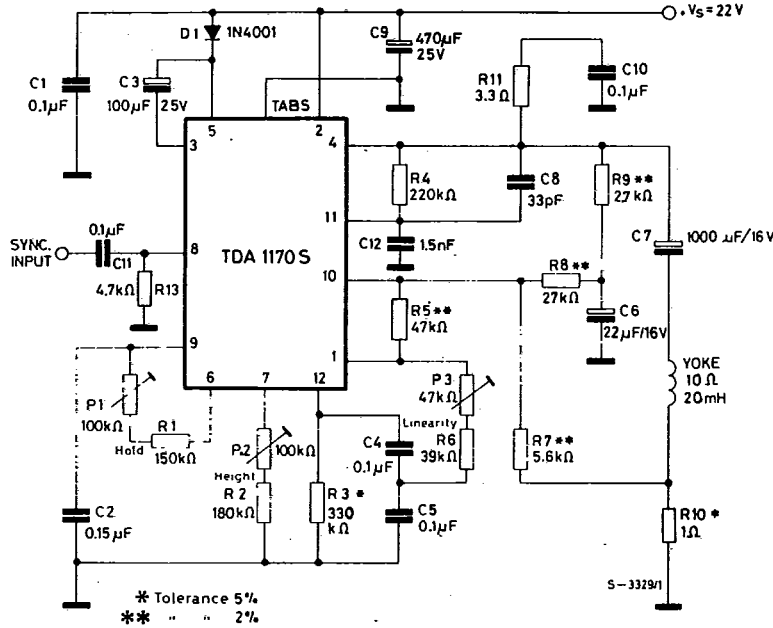
Typical performance

V_s	Operating supply voltage	22	V
I_s	Supply current	120	mA
t_{fly}	Flyback time	0.8	ms
P_{tot}	TDA 1170S power dissipation	1.95	W
I_y	Maximum scanning current (peak to peak)	1.0	A

For safe working up to $T_{amb} = 60^\circ\text{C}$ a heatsink of $R_{th} = 18^\circ\text{C/W}$ is required.



Fig. 5 - Typical application circuit for large screen B/W TV set ($R_y = 10\Omega$; $L_y = 20\text{ mH}$; $I_y = 1\text{ App}$)



Typical performance

V_s	Operating supply voltage	22	V
I_s	Supply current	145	mA
t_{fly}	Flyback time	0.7	ms
P_{tot}	TDA 1170S power dissipation	2.3	W
I_y	Maximum scanning current (peak to peak)	1.2	A

For safe working up to $T_{amb} = 60^\circ\text{C}$ a heatsink of $R_{th} = 14^\circ\text{C/W}$ is required.

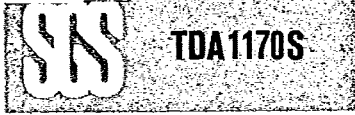
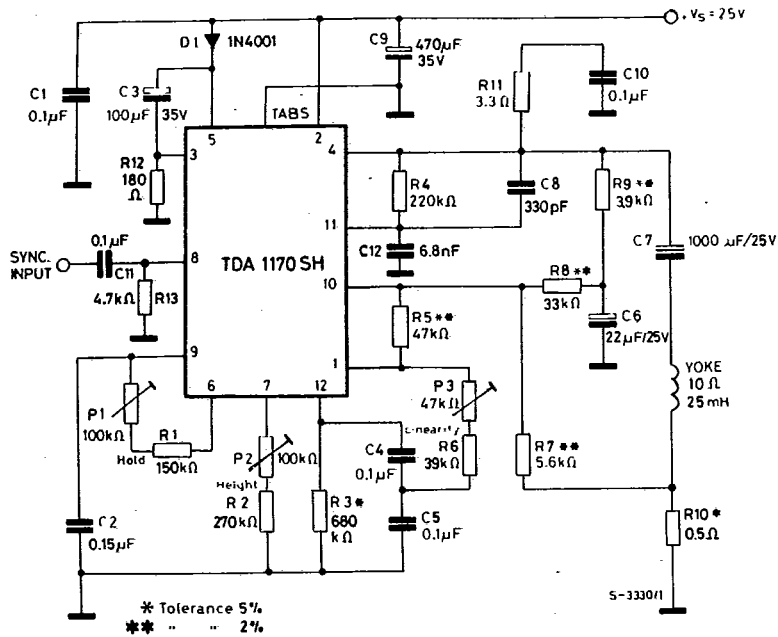


Fig. 6 - Typical application circuit for large screen 110° PIL TVC set ($R_y = 10\Omega$; $L_y = 25\text{ mH}$; $I_y = 1.25\text{ App}$)



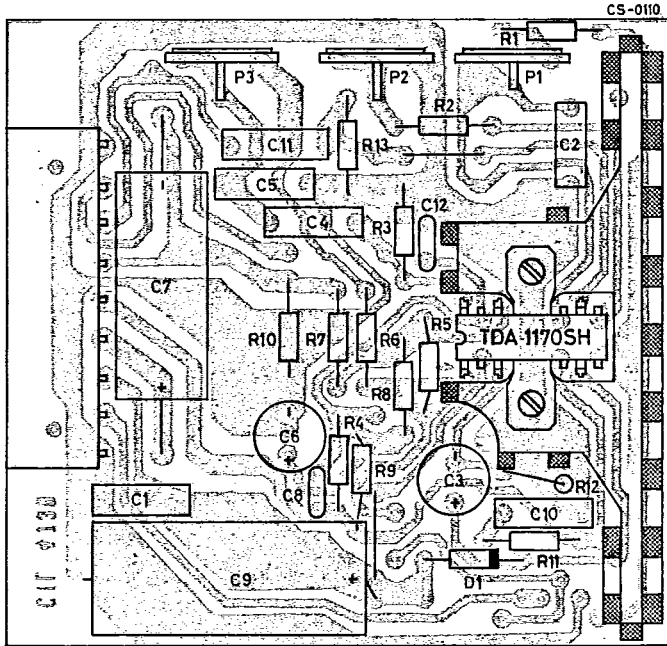
Typical performance

V_s	Operating supply voltage	25	V
I_s	Supply current	175	mA
t_{fly}	Flyback time	1	ms
P_{tot}	TDA 1170SH power dissipation	3.25	W
I_y	Maximum scanning current (peak to peak)	1.4	A

For safe working up to $T_{amb} = 60^\circ\text{C}$ a heatsink of $R_{th} = 8.5^\circ\text{C/W}$ is required.



Fig. 7 - P.C. board and component layout of the circuit of fig. 6 (1 : 1 scale)



Note: For the heatsink (1170 S and 1170 SH) see mounting instructions

MOUNTING INSTRUCTIONS

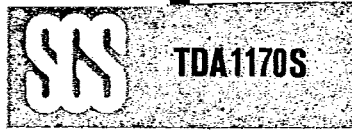
During soldering the tab temperature must not exceed 260°C and the soldering time must not be longer than 12 seconds.

The external heatsink or printed circuit copper area must be connected to electrical ground.

TDA 1170S

The junction to ambient thermal resistance of the TDA 1170S can be reduced by soldering the tabs to a suitable copper area of the printed circuit board (fig. 8) or to an external heatsink (fig. 9).

The diagram of fig. 10 shows the maximum dissippable power P_{tot} and the $R_{th j-amb}$ as a function of the side "s" of two equal square copper areas having a thickness of 35 μ (1.4 mil).



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MOUNTING INSTRUCTIONS (continued)

Fig. 8 - Example of P.C. board copper area used as heatsink.

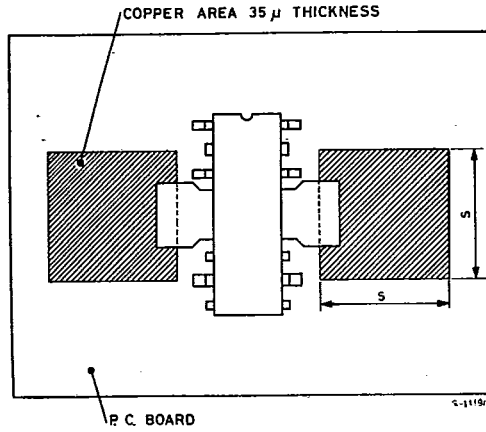


Fig. 9 - Example of TDA 1170 S with external heatsink.

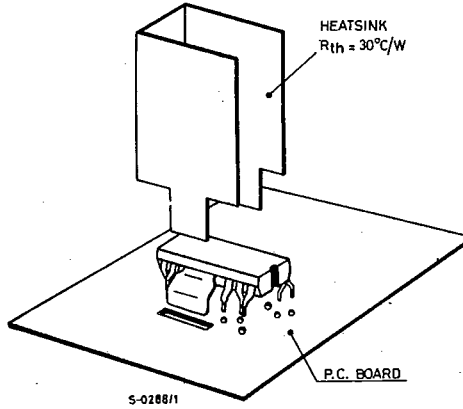


Fig. 10 - Maximum Power dissipation and junctional-ambient thermal resistance vs. "S"

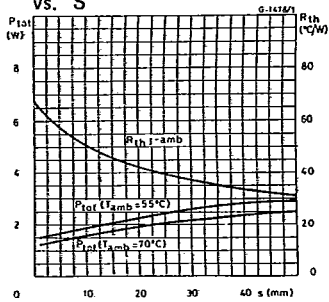


Fig. 11 - Maxim. allowable power dissipation vs. ambient temp. (TDA1170S)

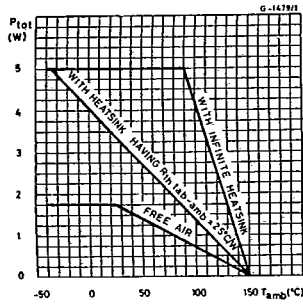
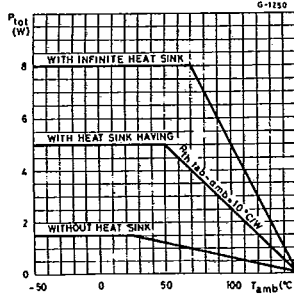
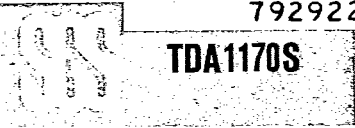


Fig. 12 - Maxim. allowable power dissipation vs. ambient temp. (TDA1170SH)



TDA 1170SH

The power dissipated in the circuit may be removed by connecting the tabs to an external heatsink according to fig. 12. The desired thermal resistance may be obtained by fixing the TDA1170SH to a suitable dimensioned plate as shown in fig. 13.



MOUNTING INSTRUCTIONS (continued)

Fig. 13 - Mounting example.

